

SC12851ZP

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| INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary) | | Application Number | 10/670928 | |
| | | Filing Date | | |
| | | First Named Inventor | Chun-Li Liu | |
| | | Group Art Unit | | |
| | | Examiner Name | D. LE 2818 | |
| Sheet | | of | Attorney Docket Number | SC12851ZP |

| U. S. PATENT DOCUMENTS | | | | | |
|------------------------|-----------------------|---|--------------------------------|--|--|
| Examiner Initials* | Cite No. ¹ | Document Number | Publication Date MM-DD-YYYY | Name of Patentee or Applicant of Cited Document | Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear |
| | | Number -Kind Code ² (if known) | | | |
| DL | AA | 5,461,243 | 10/24/1995 | Ek <i>et al.</i> | |
| | AB | 5,759,898 | 06/02/1998 | Ek <i>et al.</i> | |
| | AC | 6,369,438 B1 | 04/09/2002 | Sugiyama <i>et al.</i> | |
| | AD | 2003/0034529 A1 | 10/08/2002 | Fitzgerald | |
| | AE | 2003/0013305 A1 | 01/16/2003 | Sugii <i>et al.</i> | |
| | AF | 6,524,935 B1 | 02/25/2003 | Canaperi <i>et al.</i> | |
| DL | AG | 2003/0040160 A1 | 02/27/2003 | Huang <i>et al.</i> | |

| FOREIGN PATENT DOCUMENTS | | | | | | |
|--------------------------|-----------------------|---------------------------|--|--------------------------------|---|---|
| Examine Initials* | Cite No. ¹ | Foreign Patent Document | | Publication Date MM-DD-YYYY | Name of Patentee or Applicant of Cited Document | Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear |
| | | Country Code ³ | Number ⁴ Kind Code ² (if known) | | | |
| DL | AH | JP | 2000243946 | 12/06/1999 | Naoharu <i>et al.</i> | |
| | AI | WO | 02/33746 A1 | 04/22/2002 | Chu <i>et al.</i> | Yes/Abstract |

| NON PATENT LITERATURE DOCUMENTS | | | | | |
|---------------------------------|----------|--|--|--|----------------|
| Examiner Initials* | Cite No. | Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published. | | | T ² |
| DL | AJ | Chi <i>et al.</i> , "Electrically active defects in surface preamorphized and subsequently RTP-annealed Si and the effect of titanium silicidation," <i>Proc. 1998 5th International Conference on Solid-State and Integrated Circuit Technology</i> , October 21, 1998, Beijing, China, p. 324-327. | | | ✓ |
| | AK | Fahey <i>et al.</i> , "Point defects and dopant diffusion in silicon," <i>Reviews of Modern Physics</i> , April 1989, Vol. 61, No. 2, pp. 289-384. | | | / |
| | AL | Lee <i>et al.</i> , "Sub-30 nm P+ abrupt junction formation in Strained Si/Si _{1-x} Ge _x MOS device," <i>Technical Digest of the International Electron Devices Meeting</i> , December 8, 2002, pp. 379-81. | | | / |
| | AM | LeGoues <i>et al.</i> , "Kinetics and Mechanism of Oxidation of SiGe: Dry Versus Wet Oxidation," <i>Applied Physics Letters</i> , February 13, 1989, Vol. 54, No. 7, pp. 644-646. | | | / |
| | AN | LeGoues <i>et al.</i> , "Oxidation Studies of SiGe," <i>Journal of Applied Physics</i> , February 15, 1989, Vol. 65, No. 4, pp. 1724-1728. | | | / |
| | AO | Lim <i>et al.</i> , "Dry Thermal Oxidation of a Graded SiGe Layer," <i>Applied Physics Letters</i> , November 26, 2001, Vol. 79, No. 22, pp. 3606-3608. | | | / |
| | AP | Sawano <i>et al.</i> , "Relaxation Enhancement of SiGe Thin Layers by Ion Implantation into Si Substrates," <i>IEEE</i> , 2002, pp. 403-404. | | | / |
| | AQ | Tezuka <i>et al.</i> , "Dislocation-free Formation of Relaxed SiGe-on-insulator Layers," <i>Applied Physics Letters</i> , May 13, 2002, Vol. 80, No. 19, pp. 3560-3562. | | | / |
| | AR | Tezuka <i>et al.</i> , "Fabrication of Strained Si on an Ultrathin SiGe-on-insulator Virtual Substrate with a High-Ge Fraction," <i>Applied Physics Letters</i> , September 17, 2001, Vol. 79, No. 12, pp. 1798-1800. | | | / |
| DL | AS | Vyatkin <i>et al.</i> , "Ion Beam Induced Strain Relaxation in Pseudomorphous Epitaxial SiGe Layers," <i>IEEE</i> , 2000, pp. 70-72. | | | / |

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|-----------------------|----|--------------------|----------|
| Examiner Signature | DL | Date Considered | Feb-2005 |
|-----------------------|----|--------------------|----------|

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